



# SN65HVD25x Turbo CAN Transceivers for Higher Data Rates and Large Networks Including Features for Functional Safety

## 1 Features

- Meets the Requirements of ISO11898-2
- Turbo CAN:
  - Short and Symmetrical Propagation Delay Times and Fast Loop Times for Enhanced Timing Margin
  - Higher Data Rates in CAN Networks
- I/O Voltage Range Supports 3.3-V and 5-V MCUs
- Ideal Passive Behavior When Unpowered
  - Bus and Logic Pins are High Impedance (No Load)
  - Power Up and Power Down With Glitch-Free Operation on Bus
- Protection Features
  - HBM ESD Protection Exceeds  $\pm 12$  kV
  - Bus Fault Protection  $-27$  V to  $40$  V
  - Undervoltage Protection on Supply Pins
  - Driver Dominant Time Out (TXD DTO)
  - SN65HVD257: Receiver-Dominant Time Out (RXD DTO)
  - SN65HVD257: FAULT Output Pin
  - Thermal Shutdown Protection
- Characterized for  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$  Operation

## 2 Applications

- 1-Mbps Operation in Highly Loaded CAN Networks Down to 10-kbps Networks Using TXD DTO
- Industrial Automation, Control, Sensors, and Drive Systems
- Building, Security, and Climate Control Automation
- Telecom Base Station Status and Control
- SN65HVD257: Functional Safety With Redundant and Multitopology CAN networks
- CAN Bus Standards Such as CANopen, DeviceNet, NMEA2000, ARNIC825, ISO11783, and CANaerospace

## 3 Description

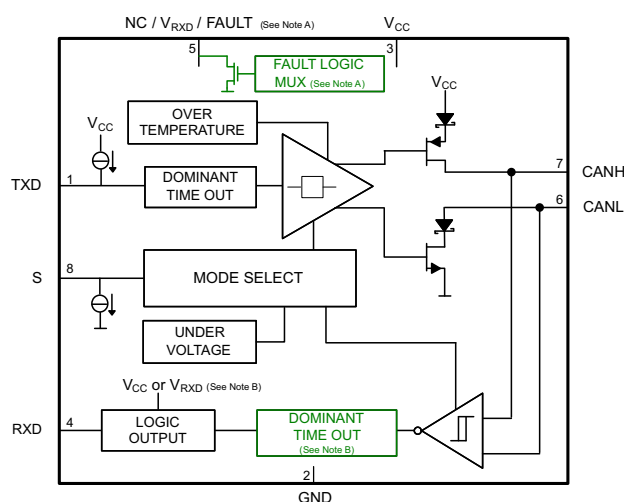
This CAN transceiver meets the ISO1189-2 High Speed CAN (Controller Area Network) Physical Layer standard. It is designed for data rates in excess of 1 Mbps for CAN in short networks, and enhanced timing margin and higher data rates in long and highly-loaded networks. The device provides many protection features to enhance device and CAN-network robustness. The SN65HVD257 device adds additional features, allowing for easy design of redundant and multitopology networks with fault indication for higher levels of functional safety in the CAN system.

### Device Information<sup>(1)</sup>

| PART NUMBER                            | PACKAGE  | BODY SIZE (NOM)   |
|--|----------|-------------------|
| SN65HVD255<br>SN65HVD256<br>SN65HVD257 | SOIC (8) | 4.90 mm x 3.91 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

### Block Diagram



- Pin 5 function is device dependent; NC on the SN65HVD255 device,  $V_{RXD}$  for RXD output level-shifting device on the SN65HVD256 device, and FAULT Output on the SN65HVD257 device.
- RXD logic output is driven to 5-V  $V_{CC}$  on 5-V only supply devices (SN65HVD255, SN65HVD257) and driven to  $V_{RXD}$  on the output level-shifting device (SN65HVD256).
- RXD (Receiver) Dominant State Time Out is a device-dependent option available only on the SN65HVD257 device.



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## 4 Revision History

### Changes from Revision C (September 2013) to Revision D Page

- Added *Pin Configuration and Functions* section, *ESD Ratings* table, *Switching Characteristics* table, *Typical Characteristics* section, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ..... **1**

### Changes from Revision B (June 2012) to Revision C Page

- Added [Table 1](#), *Receiver Differential Input Voltage Threshold Test* ..... **12**
- Added [Figure 13](#), *Example Timing Diagram for TXD DTO and FAULT Pin* ..... **17**
- Added *Bus Loading, Length, and Number of Nodes* subsection ..... **22**

### Changes from Revision A (June 2012) to Revision B Page

- Added SN65HVD257 status to production in Ordering Information table ..... **4**

### Changes from Original (December 2011) to Revision A Page

- Updated the *Features* list ..... **1**
- Updated the *Applications* list ..... **1**
- Added text to the *Description* section ..... **1**
- Changed [Block Diagram](#) - Functional Block Diagram to include HVD257 and Note changes..... **1**
- Changed the DEVICE OPTIONS table..... **4**
- Added SN65HVD257 to the D PACKAGE OPTIONS images..... **4**
- Added SN65HVD257 FAULT pin to the PIN FUNCTIONS table ..... **4**
- Added SN65HVD257 to the Ordering Information table..... **4**
- Added SN65HVD257 FAULT pin information to the Abs Max table ..... **5**
- Added FAULT pin information to the ROC table ..... **6**

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|   |    |
|---|----|
| • changed $R_{ID}$ - Differential input resistance value from 3 k $\Omega$ to 30 k $\Omega$ .....                               | 8  |
| • Added $t_{RXD\_DTO}$ - SN65HVD257 information .....   | 10 |
| • Added <a href="#">Figure 4</a> , <i>RXD Dominant Timeout Test Circuit and Measurement</i> .....                               | 11 |
| • Added <a href="#">Figure 5</a> , <i>FAULT Test and Measurement</i> .....  | 11 |
| • Added RXD Dominant Timeout (SN65HVD257) section.....  | 15 |
| • Added FAULT pin information .....   | 16 |
| • Added footnote for SN65HVD257 function to <a href="#">Table 5</a> .....   | 19 |
| • Added 5-V $V_{CC}$ with FAULT Open-Drain Output Device (SN65HVD257) section.....  | 21 |
| • Added <i>Example: Functional Safety Using the SN65HVD257 in a Redundant Physical Layer CAN Network Topology</i> section ..... | 24 |

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## SN65HVD255, SN65HVD256, SN65HVD257

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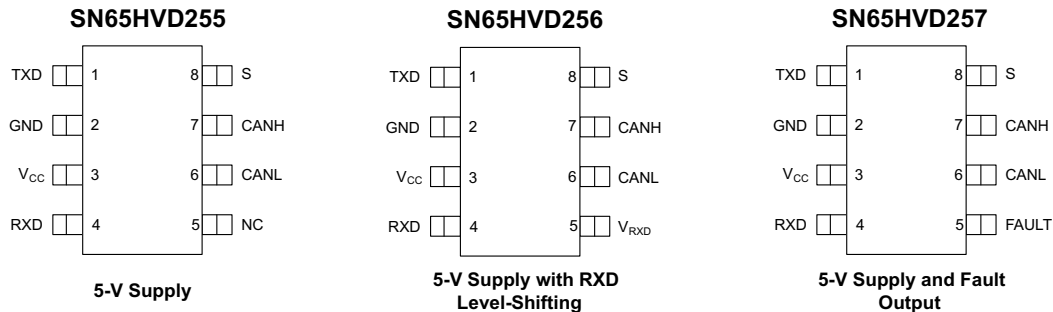
[www.ti.com](http://www.ti.com)

## 5 Device Options

| PART NUMBER | I/O SUPPLY for RXD | TXD DTO | RXD DTO | FAULT Output | COMMENT  |
|-------------|--------------------|---------|---------|--------------|--|
| SN65HVD255  | No                 | Yes     | No      | No           | '251 and '1050 functional upgrade with Turbo CAN fast loop times and TXD DTO protection allowing data rates down to 10 kbps  |
| SN65HVD256  | Yes                | Yes     | No      | No           | '251 and '1050 functional upgrade with Turbo CAN fast loop times and TXD DTO protection allowing data rates down to 10 kbps. RXD output level shifting through RXD supply input. |
| SN65HVD257  | No                 | Yes     | Yes     | Yes          | '251 and '1050 functional upgrade with Turbo CAN fast loop times, TXD and RXD DTO protection allowing data rates down to 10 kbps and fault output pin                            |

## 6 Pin Configuration and Functions

**D Package  
8-Pin SOIC  
(Top View)**



### Pin Functions

| PIN              |     | TYPE   | DESCRIPTION  |
|------------------|-----|--------|--|
| NAME             | NO. |        |  |
| TXD              | 1   | I      | CAN transmit data input (LOW for dominant and HIGH for recessive bus states) |
| GND              | 2   | GND    | Ground connection  |
| V <sub>CC</sub>  | 3   | Supply | Transceiver 5-V supply voltage   |
| RXD              | 4   | O      | CAN receive data output (LOW for dominant and HIGH for recessive bus states) |
| NC               | 5   | NC     | SN65HVD255: No Connect   |
| V <sub>RXD</sub> |     | Supply | SN65HVD256: RXD output supply voltage  |
| FAULT            |     | O      | SN65HVD257: Open drain FAULT output pin                                      |
| CANL             | 6   | I/O    | Low level CAN bus line   |
| CANH             | 7   | I/O    | High level CAN bus line  |
| S                | 8   | I      | Mode select: S (silent mode) select pin (active high)                        |

## 7 Specifications

### 7.1 Absolute Maximum Ratings<sup>(1)(2)</sup>

|                           |   |                           | MIN  | MAX  | UNIT |
|---------------------------|---|---------------------------|------|--|------|
| V <sub>CC</sub>           | Supply voltage  |                           | −0.3 | 6.1  | V    |
| V <sub>RXD</sub>          | RXD Output supply voltage   | SN65HVD256                | −0.3 | 6 and V <sub>RXD</sub> ≤ V <sub>CC</sub> + 0.3 | V    |
| V <sub>BUS</sub>          | CAN Bus I/O voltage (CANH, CANL)  |                           | −27  | 40   | V    |
| V <sub>Logic_Input</sub>  | Logic input pin voltage (TXD, S)  |                           | −0.3 | 6  | V    |
| V <sub>Logic_Output</sub> | Logic output pin voltage (RXD)  | SN65HVD255,<br>SN65HVD257 | −0.3 | 6  | V    |
| V <sub>Logic_Output</sub> | Logic output pin voltage (RXD)  | SN65HVD256                | −0.3 | 6 and V <sub>I</sub> ≤ V <sub>RXD</sub> + 0.3  | V    |
| I <sub>O(RXD)</sub>       | RXD (Receiver) output current   |                           |      | 12   | mA   |
| I <sub>O(FAULT)</sub>     | FAULT output current  | SN65HVD257                |      | 20   | mA   |
| T <sub>J</sub>            | Operating virtual junction temperature (see <a href="#">Power Dissipation</a> ) |                           | −40  | 150  | °C   |
| T <sub>A</sub>            | Ambient temperature (see <a href="#">Power Dissipation</a> )                    |                           | −40  | 125  | °C   |

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to ground terminal.

### 7.2 ESD Ratings

|                    |                         |  |   |                           | VALUE   | UNIT |
|--------------------|-------------------------|--|---|---------------------------|---------|------|
| V <sub>(ESD)</sub> | Electrostatic discharge | Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>              | All pins  |                           | ±2500   | V    |
|                    |                         |  | CAN bus pins (CANH, CANL) <sup>(2)</sup>                                    |                           | ±12000  |      |
|                    |                         | Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(3)</sup> | All pins  |                           | ±750    |      |
|                    |                         |  | Machine model   |                           | ±250    |      |
|                    |                         | IEC 61400-4-2 according to GIFT-ICT CAN EMC test spec <sup>(4)</sup>           | CAN bus pins (CANH, CANL) to GND  |                           | ±8000   |      |
|                    |                         |  | ISO7637 Transients according to GIFT - ICT CAN EMC test spec <sup>(5)</sup> | CAN bus pins (CANH, CANL) | Pulse 1 |      |
|                    |                         | Pulse 2  |   |                           | +75     |      |
|                    |                         | Pulse 3a   |   |                           | −150    |      |
| Pulse 3b           | +100                    |  |   |                           |         |      |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) Test method based upon JEDEC Standard 22 Test Method A114, CAN bus pins stressed with respect to GND.
- (3) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.
- (4) IEC 61000-4-2 is a system level ESD test. Results given here are specific to the GIFT-ICT CAN EMC Test specification conditions. Different system level configurations may lead to different results.
- (5) ISO7637 is a system level transient test. Results given here are specific to the GIFT-ICT CAN EMC Test specification conditions. Different system level configurations may lead to different results.

### 7.3 Recommended Operating Conditions

|                                   |   |            | MIN | MAX | UNIT |
|-----------------------------------|---|------------|-----|-----|------|
| V <sub>CC</sub>                   | Supply voltage  |            | 4.5 | 5.5 | V    |
| V <sub>RXD</sub>                  | RXD supply (SN65HVD256 only)  |            | 2.8 | 5.5 |      |
| V <sub>I</sub> or V <sub>IC</sub> | CAN bus terminal voltage (separately or common mode)                      |            | –2  | 7   |      |
| V <sub>ID</sub>                   | CAN bus differential voltage  |            | –6  | 6   |      |
| V <sub>IH</sub>                   | Logic HIGH level input (TXD, S)   |            | 2   | 5.5 |      |
| V <sub>IL</sub>                   | Logic LOW level input (TXD, S)  |            | 0   | 0.8 |      |
| I <sub>OH</sub> (DRVR)            | CAN BUS Driver High level output current                                  |            | –70 |     | mA   |
| I <sub>OL</sub> (DRVR)            | CAN BUS Driver Low level output current                                   |            |     | 70  |      |
| I <sub>OH</sub> (RXD)             | RXD pin HIGH level output current   |            | –2  |     |      |
| I <sub>OL</sub> (RXD)             | RXD pin LOW level output current  |            |     | 2   |      |
| I <sub>O</sub> (FAULT)            | FAULT pin LOW level output current  | SN65HVD257 |     | 2   |      |
| T <sub>A</sub>                    | Operational free-air temperature (see <a href="#">Power Dissipation</a> ) |            | –40 | 125 | °C   |

### 7.4 Thermal Information

| THERMAL METRIC <sup>(1)</sup> |  | SN65HVD25x | UNIT |
|-------------------------------|--|------------|------|
|                               |  | D (SOIC)   |      |
|                               |  | 8 PINS     |      |
| R <sub>θJA</sub>              | Junction-to-ambient thermal resistance, High-K thermal resistance <sup>(2)</sup> | 107.5      | °C/W |
| R <sub>θJC(top)</sub>         | Junction-to-case (top) thermal resistance  | 56.7       | °C/W |
| R <sub>θJB</sub>              | Junction-to-board thermal resistance   | 48.9       | °C/W |
| ψ <sub>JT</sub>               | Junction-to-top characterization parameter                                       | 12.1       | °C/W |
| ψ <sub>JB</sub>               | Junction-to-board characterization parameter                                     | 48.2       | °C/W |

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, High-K board, as specified in JESD51-7, in an environment described in JESD51-2a.

## 7.5 Electrical Characteristics

Over recommended operating conditions,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$  (unless otherwise noted). SN65HVD256 device  $V_{\text{RXD}} = V_{\text{CC}}$ .

| PARAMETER                          |   | TEST CONDITIONS                            |   | MIN                   | TYP <sup>(1)</sup> | MAX  | UNIT |   |
|------------------------------------|---|--|---|-----------------------|--------------------|------|------|---|
| SUPPLY CHARACTERISTICS             |   |  |   |                       |                    |      |      |   |
| I <sub>CC</sub>                    | 5-V Supply current  | Normal Mode (Driving Dominant)             | See Figure 6, TXD = 0 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = open, S = 0 V                          |                       | 60                 | 85   | mA   |   |
|                                    |   | Normal Mode (Driving Dominant – bus fault) | See Figure 6, TXD = 0 V, S = 0 V, CANH = −12 V, R <sub>L</sub> = open, C <sub>L</sub> = open, R <sub>CM</sub> = open            |                       | 130                | 180  |      |   |
|                                    |   | Normal Mode (Driving Dominant)             | See Figure 6, TXD = 0 V, R <sub>L</sub> = open (no load), C <sub>L</sub> = open, R <sub>CM</sub> = open, S = 0 V                |                       | 10                 | 20   |      |   |
|                                    |   | Normal Mode (Recessive)                    | See Figure 6, TXD = V <sub>CC</sub> , R <sub>L</sub> = 50 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = open, S = 0 V             |                       | 10                 | 20   |      |   |
|                                    |   | Silent Mode                                | See Figure 6, TXD = V <sub>CC</sub> , R <sub>L</sub> = 50 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = open, S = V <sub>CC</sub> |                       | 2.5                | 5    |      |   |
| I <sub>RXD</sub>                   | RXD Supply current (SN65HVD256 only)  | All modes                                  | RXD Floating, TXD = 0 V   |                       |                    | 500  | μA   |   |
| UV <sub>VCC</sub>                  | Undervoltage detection on V <sub>CC</sub> for protected mode                    |  |   | 3.5                   |                    | 4.45 | V    |   |
| V <sub>HYS(UV<sub>VCC</sub>)</sub> | Hysteresis voltage on UV <sub>VCC</sub>   |  |   |                       | 200                |      | mV   |   |
| UV <sub>RXD</sub>                  | Undervoltage detection on V <sub>RXD</sub> for protected mode (SN65HVD256 only) |  |   | 1.3                   |                    | 2.75 | V    |   |
| V <sub>HYS(UV<sub>RXD</sub>)</sub> | Hysteresis voltage on UV <sub>RXD</sub> (SN65HVD256 only)                       |  |   |                       | 80                 |      | mV   |   |
| S PIN (MODE SELECT INPUT)          |   |  |   |                       |                    |      |      |   |
| V <sub>IH</sub>                    | HIGH-level input voltage  |  |   | 2                     |                    |      | V    |   |
| V <sub>IL</sub>                    | LOW-level input voltage   |  |   |                       |                    | 0.8  | V    |   |
| I <sub>IH</sub>                    | HIGH-level input leakage current  |  | S = V <sub>CC</sub> = 5.5 V   | 7                     |                    | 100  | μA   |   |
| I <sub>IL</sub>                    | Low-level input leakage current   |  | S = 0 V, V <sub>CC</sub> = 5.5 V  | −1                    | 0                  | 1    | μA   |   |
| I <sub>LKG(OFF)</sub>              | Unpowered leakage current   |  | S = 5.5 V, V <sub>CC</sub> = 0 V, V <sub>RXD</sub> = 0 V  | 7                     | 35                 | 100  | μA   |   |
| TXD PIN (CAN TRANSMIT DATA INPUT)  |   |  |   |                       |                    |      |      |   |
| V <sub>IH</sub>                    | HIGH level input voltage  |  |   | 2                     |                    |      | V    |   |
| V <sub>IL</sub>                    | LOW level input voltage   |  |   |                       |                    | 0.8  | V    |   |
| I <sub>IH</sub>                    | HIGH level input leakage current  |  | TXD = V <sub>CC</sub> = 5.5 V   | −2.5                  | 0                  | 1    | μA   |   |
| I <sub>IL</sub>                    | Low level input leakage current   |  | TXD = 0 V, V <sub>CC</sub> = 5.5 V  | −100                  | −25                | −7   | μA   |   |
| I <sub>LKG(OFF)</sub>              | Unpowered leakage current   |  | TXD = 5.5 V, V <sub>CC</sub> = 0 V, V <sub>RXD</sub> = 0 V  | −1                    | 0                  | 1    | μA   |   |
| C <sub>I</sub>                     | Input Capacitance   |  |   |                       | 3.5                |      | pF   |   |
| RXD PIN (CAN RECEIVE DATA OUTPUT)  |   |  |   |                       |                    |      |      |   |
| V <sub>OH</sub>                    | HIGH level output voltage   |  | See Figure 7, I <sub>O</sub> = −2 mA. For devices with V <sub>RXD</sub> supply V <sub>OH</sub> = 0.8 × V <sub>RXD</sub>         | 0.8 × V <sub>CC</sub> |                    |      | V    |   |
| V <sub>OL</sub>                    | LOW level output voltage  |  | See Figure 7, I <sub>O</sub> = 2 mA   |                       |                    |      | 0.4  | V |
| I <sub>LKG(OFF)</sub>              | Unpowered leakage current   |  | RXD = 5.5 V, V <sub>CC</sub> = 0 V, V <sub>RXD</sub> = 0 V  | −1                    | 0                  | 1    | μA   |   |

(1) All typical values are at  $25^\circ\text{C}$  and supply voltages of  $V_{\text{CC}} = 5\ \text{V}$  and  $V_{\text{RXD}} = 5\ \text{V}$ ,  $R_L = 60\ \Omega$ .

## Electrical Characteristics (continued)

Over recommended operating conditions,  $T_A = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$  (unless otherwise noted). SN65HVD256 device  $V_{\text{RXD}} = V_{\text{CC}}$ .

| PARAMETER                           |   |      | TEST CONDITIONS   | MIN    | TYP <sup>(1)</sup>    | MAX   | UNIT |
|-------------------------------------|---|------|---|--------|-----------------------|-------|------|
| DRIVER ELECTRICAL CHARACTERISTICS   |   |      |   |        |                       |       |      |
| V <sub>O(D)</sub>                   | Bus output voltage (dominant)   | CANH | See Figure 15 and Figure 6, TXD = 0 V, S = 0 V, R <sub>L</sub> = 60 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = open  | 2.75   |                       | 4.5   | V    |
|                                     |   | CANL |   | 0.5    |                       | 2.25  |      |
| V <sub>O(R)</sub>                   | Bus output voltage (recessive)  |      | See Figure 15 and Figure 6, TXD = V <sub>CC</sub> , V <sub>RXD</sub> = V <sub>CC</sub> , S = V <sub>CC</sub> or 0 V <sup>(2)</sup> , R <sub>L</sub> = open (no load), R <sub>CM</sub> = open  | 2      | 0.5 × V <sub>CC</sub> | 3     | V    |
| V <sub>OD(D)</sub>                  | Differential output voltage (dominant)  |      | See Figure 15 and Figure 6, TXD = 0 V, S = 0 V, 45 Ω ≤ R <sub>L</sub> ≤ 65 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = 330 Ω, −2 V ≤ V <sub>CM</sub> ≤ 7 V, 4.75 V ≤ V <sub>CC</sub> ≤ 5.25 V | 1.5    |                       | 3     | V    |
|                                     |   |      | See Figure 15 and Figure 6, TXD = 0 V, S = 0 V, 45 Ω ≤ R <sub>L</sub> ≤ 65 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = 330 Ω, −2 V ≤ V <sub>CM</sub> ≤ 7 V, 4.5 V ≤ V <sub>CC</sub> ≤ 5.5 V   | 1.25   |                       | 3.2   |      |
| V <sub>OD(R)</sub>                  | Differential output voltage (recessive)   |      | See Figure 15 and Figure 6, TXD = V <sub>CC</sub> , S = 0 V, R <sub>L</sub> = 60 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = open   | −0.12  |                       | 0.012 | V    |
|                                     |   |      | See Figure 15 and Figure 6, TXD = V <sub>CC</sub> , S = 0 V, R <sub>L</sub> = open (no load), C <sub>L</sub> = open, R <sub>CM</sub> = open, −40°C ≤ T <sub>A</sub> ≤ 85°C                    | −0.100 |                       | 0.050 |      |
| V <sub>SYM</sub>                    | Output symmetry (dominant or recessive)<br>(V <sub>CC</sub> − V <sub>O(CANH)</sub> − V <sub>O(CANL)</sub> ) |      | See Figure 15 and Figure 6, S at 0 V, R <sub>L</sub> = 60 Ω, C <sub>L</sub> = open, R <sub>CM</sub> = open  | −0.4   |                       | 0.4   | V    |
| I <sub>OS(SS)_DOM</sub>             | Short circuit steady-state output current, Dominant   |      | See Figure 15 and Figure 11, V <sub>CANH</sub> = 0 V, CANL = open, TXD = 0 V  | −160   |                       |       | mA   |
|                                     |   |      | See Figure 15 and Figure 11, V <sub>CANL</sub> = 32 V, CANH = open, TXD = 0 V   |        |                       | 160   |      |
| I <sub>OS(SS)_REC</sub>             | Short circuit steady-state output current, Recessive  |      | See Figure 15 and Figure 11, −20 V ≤ V <sub>BUS</sub> ≤ 32 V, Where V <sub>BUS</sub> = CANH = CANL, TXD = V <sub>CC</sub> , Normal and Silent Modes   | −8     |                       | 8     | mA   |
| C <sub>O</sub>                      | Output capacitance  |      | See Input capacitance to ground (C <sub>I</sub> ) in the following <i>Receiver Electrical Characteristics</i> section of this table   |        |                       |       |      |
| RECEIVER ELECTRICAL CHARACTERISTICS |   |      |   |        |                       |       |      |
| V <sub>IT+</sub>                    | Positive-going input threshold voltage, normal mode   |      | See Figure 7, Table 5 and Table 1   |        |                       | 900   | mV   |
| V <sub>IT−</sub>                    | Negative-going input threshold voltage, normal mode   |      |   | 500    |                       |       | mV   |
| V <sub>HYS</sub>                    | Hysteresis voltage (V <sub>IT+</sub> - V <sub>IT−</sub> )   |      |   |        |                       | 125   | mV   |
| I <sub>IOFF(LKG)</sub>              | Power-off (unpowered) bus input leakage current   |      | V <sub>CANH</sub> = V <sub>CANL</sub> = 5 V, V <sub>CC</sub> = 0 V, V <sub>RXD</sub> = 0 V  |        |                       | 5.5   | μA   |
| C <sub>I</sub>                      | Input capacitance to ground (CANH or CANL)  |      | TXD = V <sub>CC</sub> , V <sub>RXD</sub> = V <sub>CC</sub> , V <sub>I</sub> = 0.4 sin (4E6 π t) + 2.5 V   |        |                       | 25    | pF   |
| C <sub>ID</sub>                     | Differential input capacitance  |      | TXD = V <sub>CC</sub> , V <sub>RXD</sub> = V <sub>CC</sub> , V <sub>I</sub> = 0.4 sin (4E6 π t)   |        |                       | 10    | pF   |
| R <sub>ID</sub>                     | Differential input resistance   |      | TXD = V <sub>CC</sub> = V <sub>RXD</sub> = 5 V, S = 0 V   | 30     |                       | 80    | kΩ   |
| R <sub>IN</sub>                     | Input resistance (CANH or CANL)   |      |   | 15     |                       | 40    | kΩ   |
| R <sub>IN(M)</sub>                  | Input resistance matching:<br>[1 − R <sub>IN(CANH)</sub> / R <sub>IN(CANL)</sub> ] × 100%                   |      | V <sub>(CANH)</sub> = V <sub>(CANL)</sub> , −40°C ≤ T <sub>A</sub> ≤ 85°C   | −3%    |                       | 3%    |      |

(2) For the bus output voltage (recessive) will be the same if the device is in normal mode with S pin LOW or if the device is in silent mode with the S pin HIGH.



## Electrical Characteristics (continued)

Over recommended operating conditions,  $T_A = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$  (unless otherwise noted). SN65HVD256 device  $V_{\text{RXD}} = V_{\text{CC}}$ .

| PARAMETER  | TEST CONDITIONS                        | MIN | TYP <sup>(1)</sup> | MAX | UNIT          |
|--|--|-----|--------------------|-----|---------------|
| <b>FAULT PIN (FAULT OUTPUT), SN65HVD257 ONLY</b> |  |     |                    |     |               |
| $I_{\text{CH}}$ Output current high level        | FAULT = $V_{\text{CC}}$ , see Figure 5 | -10 |                    | 10  | $\mu\text{A}$ |
| $I_{\text{CL}}$ Output current low level         | FAULT = 0.4 V, see Figure 5            | 5   | 12                 |     | mA            |

## 7.6 Power Dissipation

| THERMAL METRIC                  | TEST CONDITIONS   | TYP | UNIT               |
|---------------------------------|---|-----|--------------------|
| $P_D$ Average power dissipation | $V_{\text{CC}} = 5\text{ V}$ , $V_{\text{RXD}} = 5\text{ V}$ , $T_J = 27^{\circ}\text{C}$ , $R_L = 60\ \Omega$ , S at 0 V, Input to TXD at 250 kHz, 25% duty cycle square wave, $C_{L\_RXD} = 15\text{ pF}$ . Typical CAN operating conditions at 500 kbps with 25% transmission (dominant) rate.                                 | 115 | mW                 |
|                                 | $V_{\text{CC}} = 5.5\text{ V}$ , $V_{\text{RXD}} = 5.5\text{ V}$ , $T_J = 150^{\circ}\text{C}$ , $R_L = 50\ \Omega$ , S at 0 V, Input to TXD at 500 kHz, 50% duty cycle square wave, $C_{L\_RXD} = 15\text{ pF}$ . Typical high load CAN operating conditions at 1 Mbps with 50% transmission (dominant) rate and loaded network. | 268 |                    |
| Thermal shutdown temperature    |   | 170 | $^{\circ}\text{C}$ |
| Thermal shutdown hysteresis     |   | 5   | $^{\circ}\text{C}$ |

## 7.7 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

| PARAMETER   | TEST CONDITIONS   | MIN  | TYP | MAX  | UNIT          |
|---|---|------|-----|------|---------------|
| <b>DEVICE SWITCHING CHARACTERISTICS</b>   |   |      |     |      |               |
| $t_{\text{PROP(LOOP1)}}$ Total loop delay, driver input (TXD) to receiver output (RXD), recessive to dominant | See Figure 9, S = 0 V, $R_L = 60\ \Omega$ , $C_L = 100\text{ pF}$ , $C_{L\_RXD} = 15\text{ pF}$         |      |     | 150  | ns            |
| $t_{\text{PROP(LOOP2)}}$ Total loop delay, driver input (TXD) to receiver output (RXD), dominant to recessive |   |      |     | 150  |               |
| $I_{\text{MODE}}$ Mode change time, from Normal to Silent or from Silent to Normal                            | See Figure 8  |      |     | 20   | $\mu\text{S}$ |
| <b>DRIVER SWITCHING CHARACTERISTICS</b>   |   |      |     |      |               |
| $t_{\text{pHR}}$ Propagation delay time, HIGH TXD to Driver Recessive   | See Figure 6, S = 0 V, $R_L = 60\ \Omega$ , $C_L = 100\text{ pF}$ , $R_{\text{CM}} = \text{open}$       |      | 50  | 70   | ns            |
| $t_{\text{pLD}}$ Propagation delay time, LOW TXD to Driver Dominant   |   |      | 40  | 70   |               |
| $t_{\text{sk(p)}}$ Pulse skew ( $ t_{\text{pHR}} - t_{\text{pLD}} $ )   |   |      | 10  |      |               |
| $t_{\text{R}}$ Differential output signal rise time   |   |      | 10  | 30   |               |
| $t_{\text{F}}$ Differential output signal fall time   |   |      | 17  | 30   |               |
| $t_{\text{R(10k)}}$ Differential output signal rise time, $R_L = 10\text{ k}\Omega$                           | See Figure 6, S = 0 V, $R_L = 10\text{ k}\Omega$ , $C_L = 10\text{ pF}$ , $R_{\text{CM}} = \text{open}$ |      |     | 35   | ns            |
| $t_{\text{F(10k)}}$ Differential output signal fall time, $R_L = 10\text{ k}\Omega$                           |   |      |     | 100  |               |
| $t_{\text{TXD\_DTO}}$ Dominant timeout <sup>(1)</sup>   | See Figure 10, $R_L = 60\ \Omega$ , $C_L = \text{open}$   | 1175 |     | 3700 | $\mu\text{s}$ |

- (1) The TXD dominant timeout ( $t_{\text{TXD\_DTO}}$ ) disables the driver of the transceiver when the TXD has been dominant longer than  $t_{\text{TXD\_DTO}}$ , which releases the bus lines to recessive, thus preventing a local failure from locking the bus dominant. The driver may only transmit dominant again after TXD has been returned HIGH (recessive). While this protects the bus from local faults locking the bus dominant, it limits the minimum data rate possible. The CAN protocol allows a maximum of eleven successive dominant bits (on TXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the  $t_{\text{TXD\_DTO}}$  minimum, limits the minimum bit rate. The minimum bit rate may be calculated by: Minimum Bit Rate =  $11 / t_{\text{TXD\_DTO}} = 11\text{ bits} / 1175\ \mu\text{s} = 9.4\text{ kbps}$ .

## Switching Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

| PARAMETER                                 |   | TEST CONDITIONS                    | MIN  | TYP | MAX  | UNIT    |
|---|---|------------------------------------|------|-----|------|---------|
| <b>RECEIVER SWITCHING CHARACTERISTICS</b> |   |                                    |      |     |      |         |
| $t_{pRH}$                                 | Propagation delay time, recessive input to high output                          | See Figure 7, $C_{L\_RXD} = 15$ pF |      | 70  | 90   | ns      |
| $t_{pDL}$                                 | Propagation delay time, dominant input to low output                            |                                    |      | 70  | 90   | ns      |
| $t_R$                                     | Output signal rise time   |                                    |      | 4   | 20   | ns      |
| $t_F$                                     | Output signal fall time   |                                    |      | 4   | 20   | ns      |
| $t_{RXD\_DTO}^{(2)}$                      | Receiver dominant time out (SN65HVD257 only) See Figure 4, $C_{L\_RXD} = 15$ pF |                                    | 1380 |     | 4200 | $\mu$ s |

- (2) The RXD timeout ( $t_{RXD\_DTO}$ ) disables the RXD output in the case that the bus has been dominant longer than  $t_{RXD\_DTO}$ , which releases RXD pin to the recessive state (high), thus preventing a dominant bus failure from permanently keeping the RXD pin low. The RXD pin will automatically resume normal operation once the bus has been returned to a recessive state. While this protects the protocol controller from a permanent dominant state, it limits the minimum data rate possible. The CAN protocol allows a maximum of eleven successive dominant bits (on RXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the  $t_{RXD\_DTO}$  minimum, limits the minimum bit rate. The minimum bit rate may be calculated by: Minimum Bit Rate =  $11 / t_{RXD\_DTO} = 11 \text{ bits} / 1380 \mu\text{s} = 8 \text{ kbps}$ .

## 7.8 Typical Characteristics

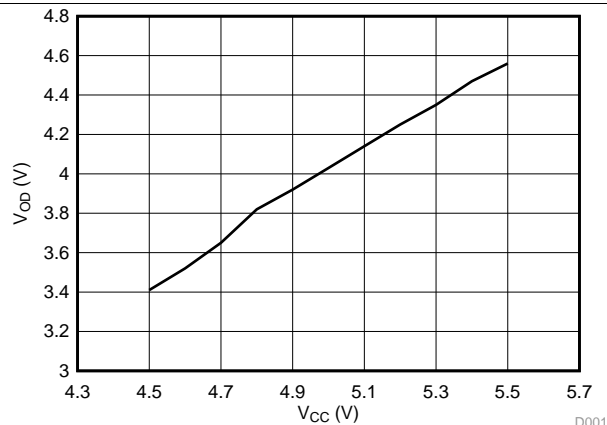


Figure 1. Differential Output Voltage vs Supply Voltage

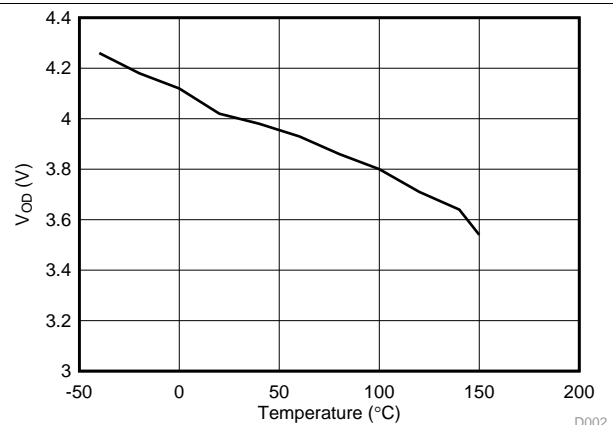


Figure 2. Differential Output Voltage vs Ambient Temperature

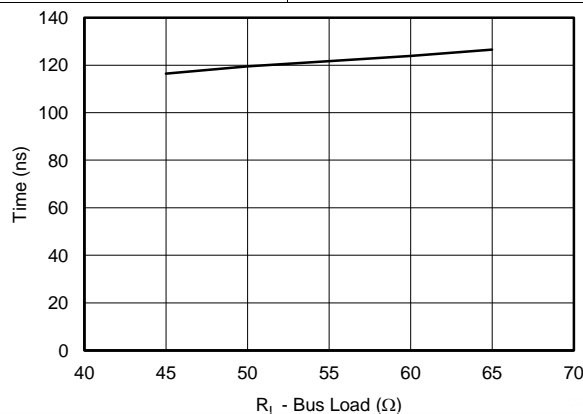


Figure 3. Typical Transceiver Loop Delay vs Bus Loading

## 8 Parameter Measurement Information

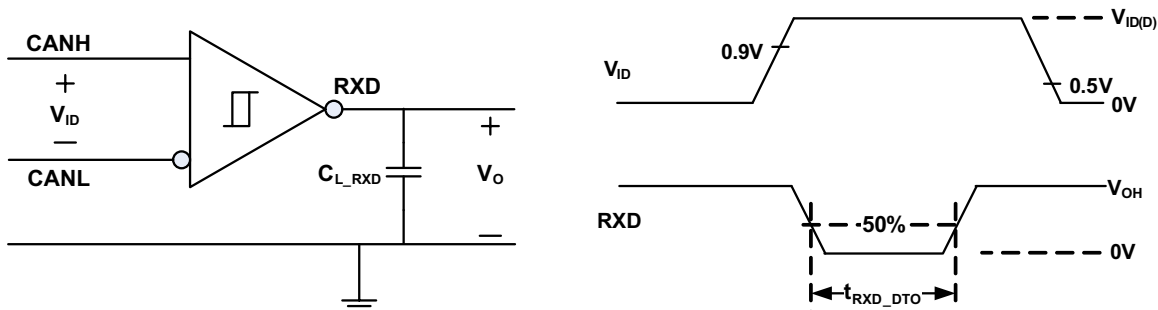


Figure 4. RXD Dominant Timeout Test Circuit and Measurement

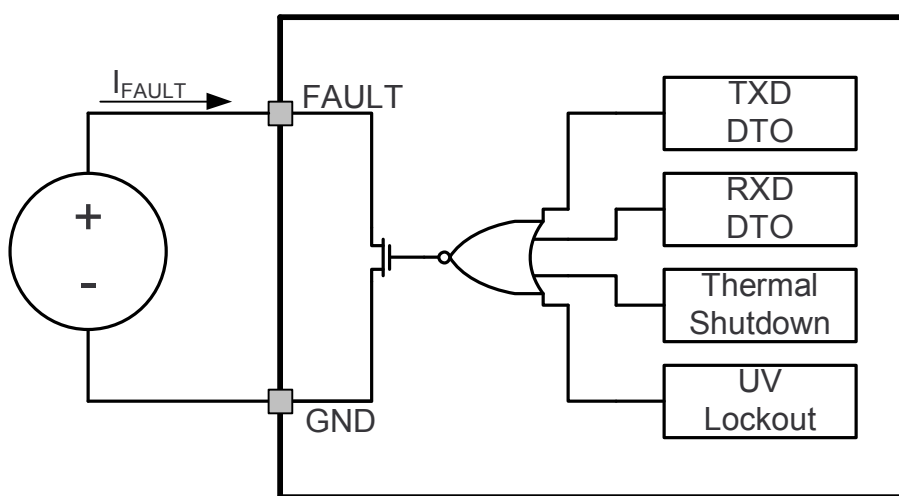


Figure 5. FAULT Test and Measurement

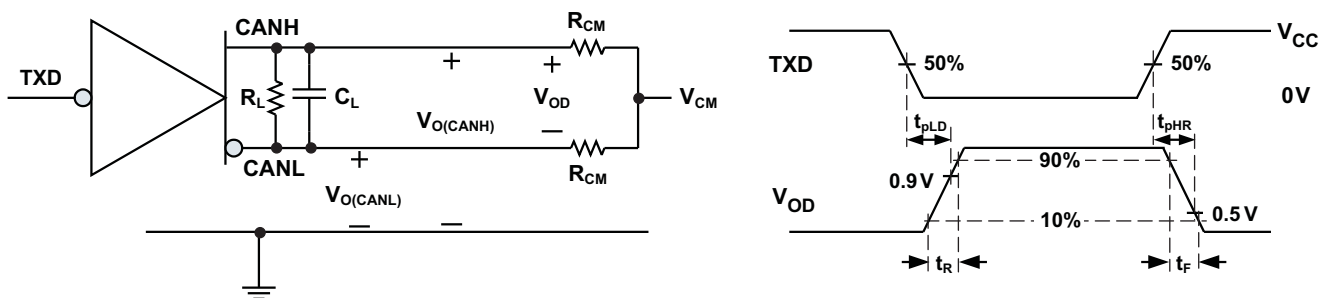
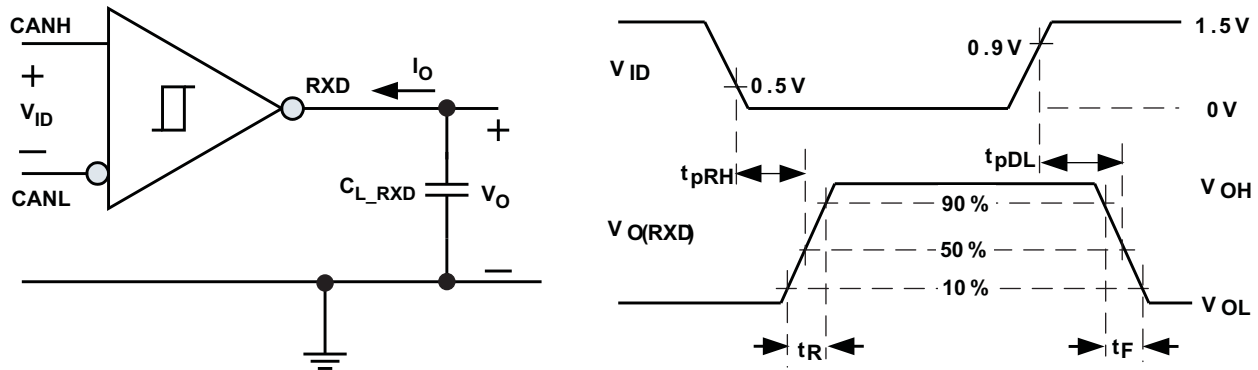
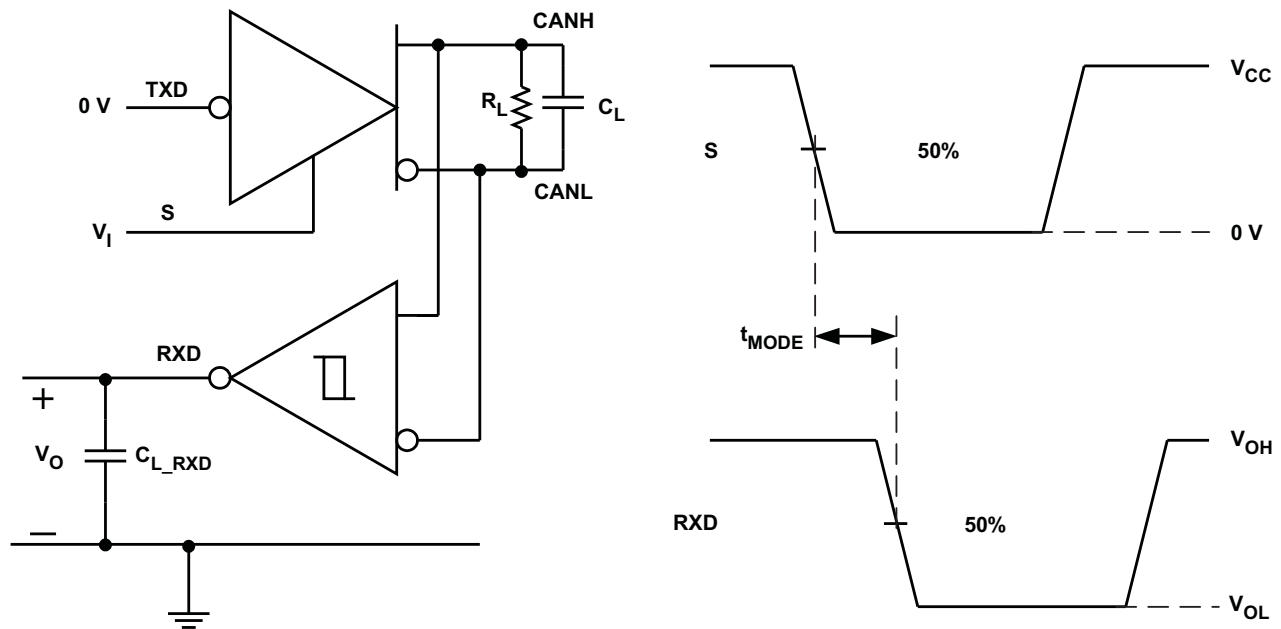


Figure 6. Driver Test Circuit and Measurement

**Parameter Measurement Information (continued)**

**Figure 7. Receiver Test Circuit and Measurement**

**Figure 8.  $t_{MODE}$  Test Circuit and Measurement**
**Table 1. Receiver Differential Input Voltage Threshold Test**

| INPUT      |            |            | OUTPUT   |          |
|------------|------------|------------|----------|----------|
| $V_{CANH}$ | $V_{CANL}$ | $ V_{ID} $ | $R_{XD}$ |          |
| -1.1 V     | -2.0 V     | 900 mV     | L        | $V_{OL}$ |
| 7.0 V      | 6.1 V      | 900 mV     | L        |          |
| -1.5 V     | -2.0 V     | 500 mV     | H        | $V_{OH}$ |
| 7.0 V      | 6.5 V      | 500 mV     | H        |          |
| Open       | Open       | X          | H        |          |

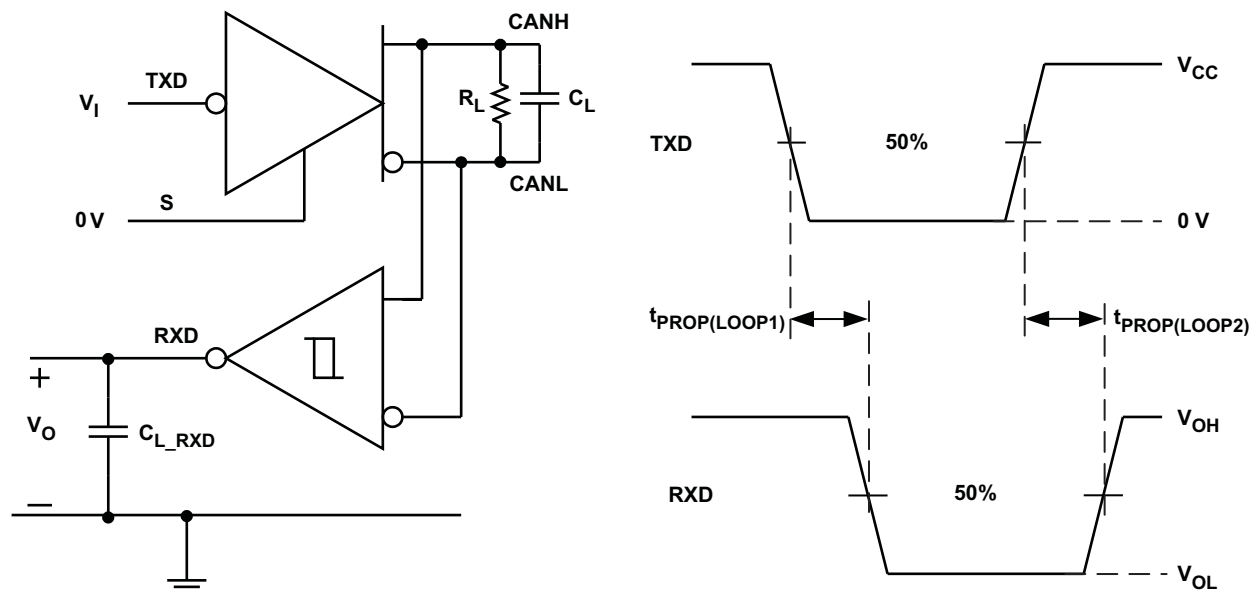


Figure 9.  $T_{PROP(LOOP)}$  Test Circuit and Measurement

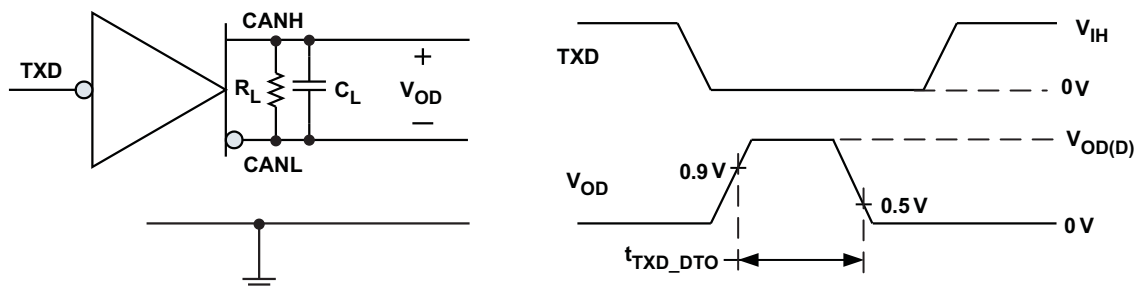


Figure 10. TXD Dominant Timeout Test Circuit and Measurement

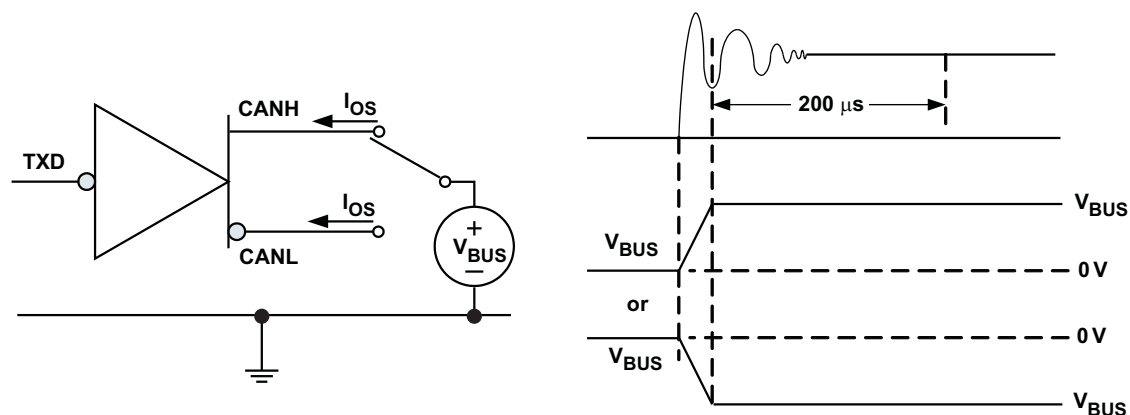


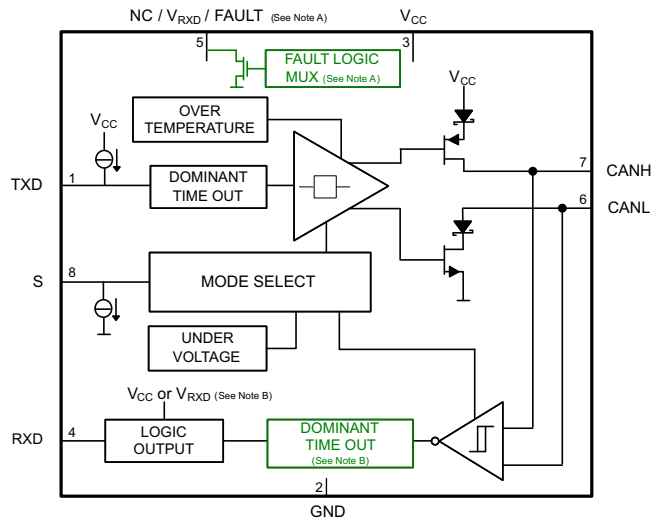
Figure 11. Driver Short Circuit Current Test and Measurement

## 9 Detailed Description

### 9.1 Overview

The SN65HVD25x family of bus transceiver devices are compatible with the ISO 11898-2 High Speed CAN (Controller Area Network) physical layer standard. The SN65HVD25x devices are designed to interface between the differential bus lines and the CAN protocol controller at data rates up to 1 Mbps (megabits per second).

### 9.2 Functional Block Diagram



- Pin 5 function is device dependent; NC on SN65HVD255,  $V_{RXD}$  for RXD output level-shifting device on the SN65HVD256 device, and FAULT Output on the SN65HVD257 device.
- RXD logic output is driven to 5-V  $V_{CC}$  on 5-V only supply devices (SN65HVD255, SN65HVD257) and driven to  $V_{RXD}$  on output level-shifting device (SN65HVD256).
- RXD (Receiver) Dominant State Time Out is a device dependent option available only on the SN65HVD257 device.

### 9.3 Feature Description

#### 9.3.1 TXD Dominant Timeout (DTO)

During normal mode (the only mode where the CAN driver is active), the TXD DTO circuit prevents the transceiver from blocking network communication in the event of a hardware or software failure where TXD is held dominant longer than the timeout period  $t_{TXD\_DTO}$ . The DTO circuit timer starts on a falling edge on TXD. The DTO circuit disables the CAN bus driver if no rising edge is seen before the timeout period expires, which frees the bus for communication between other nodes on the network. The CAN driver is reactivated when a recessive signal is seen on TXD pin, thus clearing the TXD DTO condition. The receiver and RXD pin still reflect the CAN bus, and the bus pins are biased to recessive level during a TXD dominant timeout.

#### NOTE

The minimum dominant TXD time allowed by the TXD DTO circuit limits the minimum possible transmitted data rate of the device. The CAN protocol allows a maximum of eleven successive dominant bits (on TXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the  $t_{TXD\_DTO}$  minimum, limits the minimum data rate. Calculate the minimum transmitted data rate by:  
Minimum Data Rate =  $11 / t_{TXD\_DTO}$ .

## Feature Description (continued)

### 9.3.2 RXD Dominant Timeout (SN65HVD257)

The SN65HVD257 device has a RXD dominant timeout (RXD DTO) circuit that prevents a bus stuck dominant fault from permanently driving the RXD output dominant (low) when the bus is held dominant longer than the timeout period  $t_{RXD\_DTO}$ . The RXD DTO timer starts on a falling edge on RXD (bus going dominant). If no rising edge (bus returning recessive) is seen before the timeout constant of the circuit expires ( $t_{RXD\_DTO}$ ), the RXD pin returns high (recessive). The RXD output is reactivated to mirror the bus receiver output when a recessive signal is seen on the bus, clearing the RXD dominant timeout. The CAN bus pins are biased to the recessive level during a RXD DTO.

#### NOTE

The minimum dominant RXD time allowed by the RXD DTO limits the minimum possible received data rate of the device. The CAN protocol allows a maximum of eleven successive dominant bits for the worst case transmission, where five successive dominant bits are followed immediately by an error frame. This, along with the  $t_{RXD\_DTO}$  minimum, limits the minimum data rate. The minimum received data rate may be calculated by:  
Minimum Data Rate =  $11 / t_{RXD\_DTO}$ .

### 9.3.3 Thermal Shutdown

If the junction temperature of the device exceeds the thermal shut down threshold, the device turns off the CAN driver circuits thus blocking the TXD to bus transmission path. The shutdown condition is cleared when the junction temperature drops below the thermal shutdown temperature of the device.

#### NOTE

During thermal shutdown the CAN bus drivers turn off; thus, no transmission is possible from TXD to the bus. The CAN bus pins are biased to recessive level during a thermal shutdown, and the receiver to RXD path remains operational.

### 9.3.4 Undervoltage Lockout

The supply pins have undervoltage detection that places the device in protected mode, which protects the bus during an undervoltage event on either the  $V_{CC}$  or  $V_{RXD}$  supply pins.

**Table 2. Undervoltage Lockout 5-V Only Devices (SN65HVD255 and SN65HVD257)**

| $V_{CC}$ | DEVICE STATE | BUS OUTPUT               | RXD                      |
|----------|--------------|--------------------------|--------------------------|
| GOOD     | Normal       | Per Device State and TXD | Mirrors Bus              |
| BAD      | Protected    | High Impedance           | High Impedance (3-state) |

**Table 3. Undervoltage Lockout 5 V and  $V_{RXD}$  Device (SN65HVD256)**

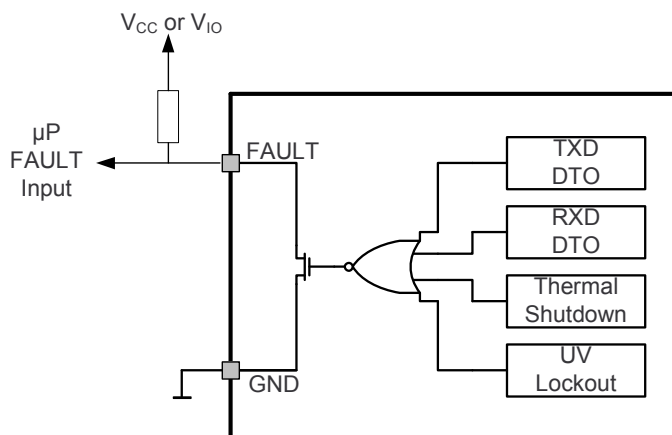
| $V_{CC}$ | $V_{RXD}$ | DEVICE STATE | BUS OUTPUT               | RXD                      |
|----------|-----------|--------------|--------------------------|--------------------------|
| GOOD     | GOOD      | Normal       | Per Device State and TXD | Mirrors Bus              |
| BAD      | GOOD      | Protected    | High Impedance           | High (Recessive)         |
| GOOD     | BAD       | Protected    | Recessive                | High Impedance (3-state) |
| BAD      | BAD       | Protected    | High Impedance           | High Impedance (3-state) |

**NOTE**

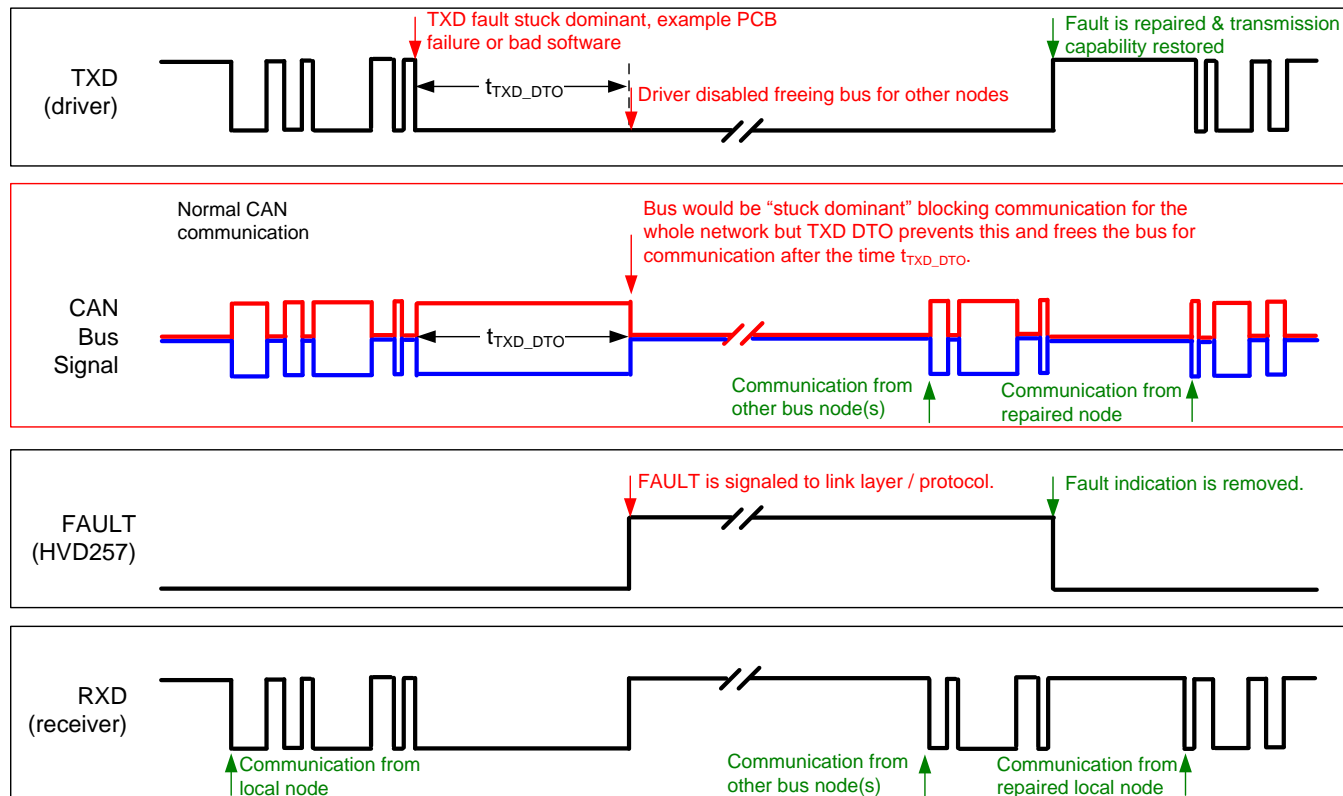
After an undervoltage condition is cleared and the supplies have returned to valid levels, the device typically resumes normal operation in 300  $\mu$ s.

**9.3.5 FAULT Pin (SN65HVD257)**

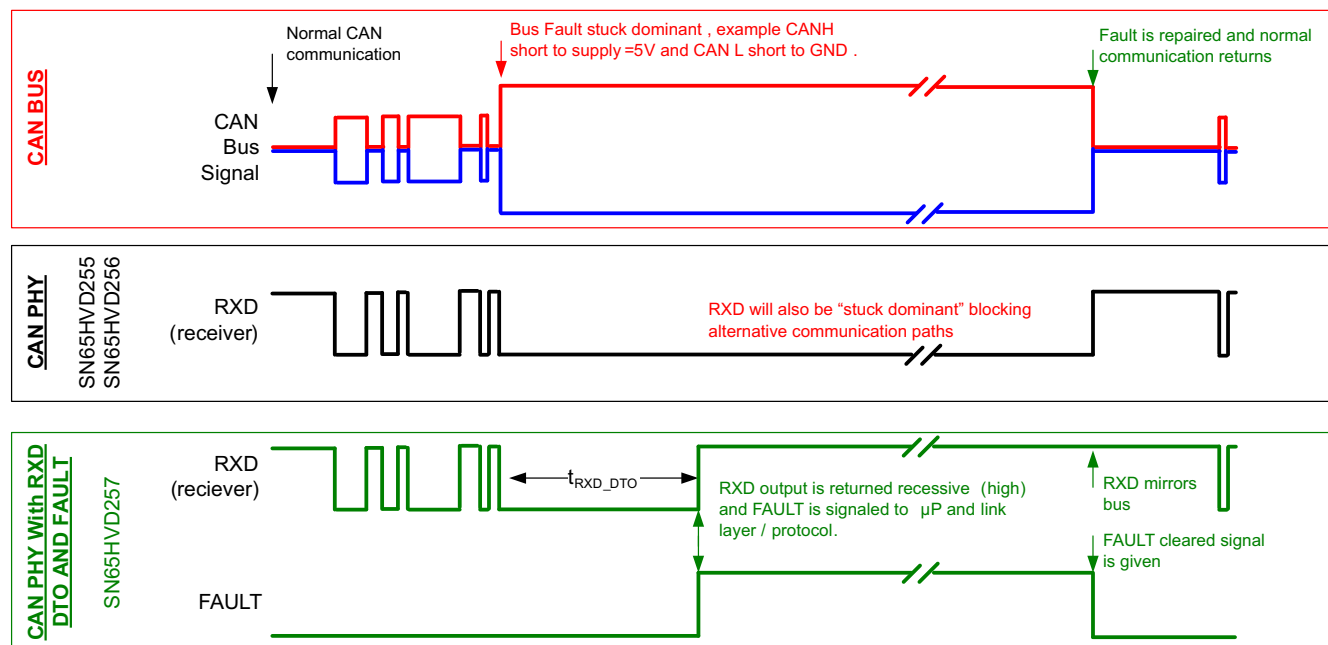
If one or more of the faults (TXD dominant timeout, RXD dominant timeout, thermal shutdown or undervoltage lockout) occurs, the FAULT pin (open-drain) turns off, resulting in a high level when externally pulled up to  $V_{CC}$  or I/O supply.


**Figure 12. FAULT Pin Function Diagram and Application**





**Figure 13. Example Timing Diagram for TXD DTO and FAULT Pin**



**Figure 14. Example Timing Diagram for Devices With and Without RXD DTO and FAULT Pin**

### 9.3.6 Unpowered Device

The SN65HVD25x device is designed to be an *ideal passive* or *no load* to the CAN bus if it is unpowered. The bus pins (CANH, CANL) have extremely low leakage currents when the device is unpowered, so they will not load down the bus. This is critical if some nodes of the network will be unpowered while the rest of the network remains in operation. The logic pins also have extremely low leakage currents when the device is unpowered to avoid loading down other circuits that may remain powered.

### 9.3.7 Floating Pins

The device has internal pullups and pulldowns on critical pins to place the device into known states if the pins float. The TXD pin is pulled up to  $V_{CC}$  to force a recessive input level if the pin floats. The S pin is pulled down to GND to force the device into normal mode if the pin floats.

### 9.3.8 CAN Bus Short-Circuit Current Limiting

The SN65HVD25x device has several protection features that limit the short circuit current when a CAN bus line is shorted. These features include driver current limiting (dominant and recessive). The device has TXD dominant state time out to prevent permanent higher short circuit current of the dominant state during a system fault. During CAN communication, the bus switches between dominant and recessive states with the data and control fields bits; thus the short circuit current may be viewed either as the instantaneous current during each bus state or as a DC average current. For system current (power supply) and power considerations in the termination resistors and common-mode choke ratings, use the average short circuit current. Determine the ratio of dominant and recessive bits by the data in the CAN frame plus the following factors of the protocol and PHY that force either recessive or dominant at the following times:

- Control fields with set bits
- Bit stuffing
- Interframe space
- TXD dominant time out (fault case limiting)

These factors ensure a minimum recessive amount of time on the bus even if the data field contains a high percentage of dominant bits.

The short circuit current of the bus depends on the ratio of recessive to dominant bits and their respective short circuit currents. The average short circuit current may be calculated with [Equation 1](#).

$$I_{OS(AVG)} = \%Transmit \times [(\%REC\_Bits \times I_{OS(SS\_REC)}) + (\%DOM\_Bits \times I_{OS(SS\_DOM)})] + [\%Receive \times I_{OS(SS\_REC)}] \quad (1)$$

where:

$I_{OS(AVG)}$  is the average short circuit current

%Transmit is the percentage the node is transmitting CAN messages

%Receive is the percentage the node is receiving CAN messages

%REC\_Bits is the percentage of recessive bits in the transmitted CAN messages

%DOM\_Bits is the percentage of dominant bits in the transmitted CAN messages

$I_{OS(SS\_REC)}$  is the recessive steady state short circuit current

$I_{OS(SS\_DOM)}$  is the dominant steady state short circuit current

#### NOTE

Consider the short circuit current and possible fault cases of the network when sizing the power ratings of the termination resistance and other network components.

## 9.4 Device Functional Modes

**Table 4. Driver Function Table**

| DEVICE      | INPUTS              |                       | OUTPUTS             |                     | DRIVEN BUS STATE |
|-------------|---------------------|-----------------------|---------------------|---------------------|------------------|
|             | S <sup>(1)(2)</sup> | TXD <sup>(1)(3)</sup> | CANH <sup>(1)</sup> | CANL <sup>(1)</sup> |                  |
| All Devices | L or Open           | L                     | H                   | L                   | Dominant         |
|             |                     | H or Open             | Z                   | Z                   | Recessive        |
|             | H                   | X                     | Z                   | Z                   | Recessive        |

(1) H = high level, L = low level, X = irrelevant, Z = common mode (recessive) bias to  $V_{CC} / 2$ . See [Figure 15](#) and [Figure 16](#) for bus state and common mode bias information.

(2) Devices have an internal pulldown to GND on S pin. If S pin is open the pin will be pulled low and the device will be in normal mode.

(3) Devices have an internal pullup to  $V_{CC}$  on TXD pin. If the TXD pin is open the pin will be pulled high and the transmitter will remain in recessive (nondriven) state.

**Table 5. Receiver Function Table**

| DEVICE MODE      | CAN DIFFERENTIAL INPUTS<br>$V_{ID} = V_{CANH} - V_{CANL}$ | BUS STATE | RXD PIN <sup>(1)</sup> |
|------------------|---|-----------|------------------------|
| Normal or Silent | $V_{ID} \geq 0.9 \text{ V}$                               | Dominant  | L <sup>(2)</sup>       |
|                  | $0.5 \text{ V} < V_{ID} < 0.9 \text{ V}$                  | ?         | ?                      |
|                  | $V_{ID} \leq 0.5 \text{ V}$                               | Recessive | H                      |
|                  | Open ( $V_{ID} \approx 0 \text{ V}$ )                     | Open      | H                      |

(1) H = high level, L = low level, ? = indeterminate.

(2) RXD output remains dominant (low) as long as the bus is dominant. On the SN65HVD257 device with RXD dominant timeout, when the bus has been dominant longer than the dominant timeout,  $t_{RXD\_DTO}$ , the RXD pin will return recessive (high). See [RXD Dominant Timeout \(SN65HVD257\)](#) for a description of behavior during receiving a bus stuck dominant condition.

### 9.4.1 Operating Modes

The device has two main operating modes: normal mode and silent mode. Operating mode selection is made via the S input pin.

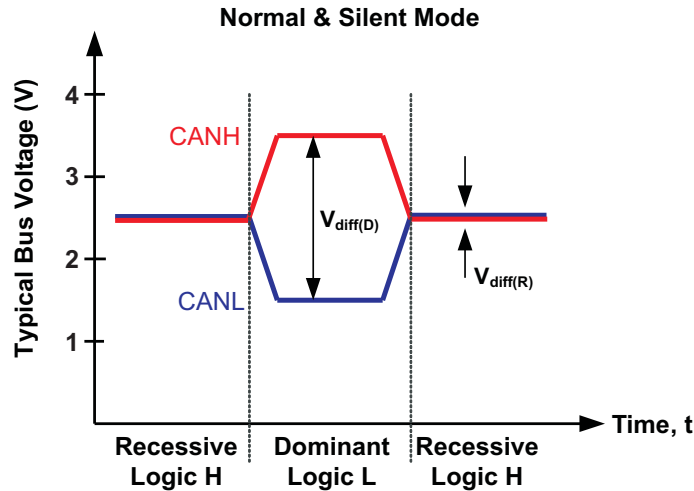
**Table 6. Operating Modes**

| S Pin | MODE        | DRIVER         | RECEIVER     | RXD PIN                          |
|-------|-------------|----------------|--------------|----------------------------------|
| LOW   | Normal Mode | Enabled (ON)   | Enabled (ON) | Mirrors Bus State <sup>(1)</sup> |
| HIGH  | Silent Mode | Disabled (OFF) | Enabled (ON) | Mirrors Bus State                |

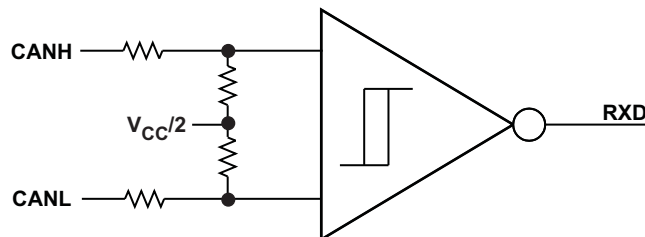
(1) Mirrors bus state: low if CAN bus is dominant, high if CAN bus is recessive.

### 9.4.2 Can Bus States

The CAN bus has two states during powered operation of the device: *dominant* and *recessive*. A dominant bus state is when the bus is driven differentially, corresponding to a logic low on the TXD and RXD pin. A recessive bus state is when the bus is biased to  $V_{CC} / 2$  via the high-resistance internal input resistors  $R_{IN}$  of the receiver, corresponding to a logic high on the TXD and RXD pins. See [Figure 15](#) and [Figure 16](#).



**Figure 15. Bus States (Physical Bit Representation)**



**Figure 16. Simplified Recessive Common Mode Bias and Receiver**

### 9.4.3 Normal Mode

Select the normal mode of device operation by setting S low. The CAN driver and receiver are fully operational and CAN communication is bidirectional. The driver is translating a digital input on TXD to a differential output on CANH and CANL. The receiver is translating the differential signal from CANH and CANL to a digital output on RXD.

### 9.4.4 Silent Mode

Activate silent mode (receive only) by setting S high. The CAN driver is turned off while the receiver remains active and RXD outputs the received bus state.

#### NOTE

Silent mode may be used to implement babbling idiot protection, to ensure that the driver does not disrupt the network during a local fault. Silent mode may also be used in redundant systems to select or de-select the redundant transceiver (driver) when needed.

## 9.4.5 Digital Inputs and Outputs

### 9.4.5.1 5-V $V_{CC}$ Only Devices (SN65HVD255 and SN65HVD257)

The 5-V  $V_{CC}$  device is supplied by a single 5-V rail. The digital inputs are 5-V and 3.3-V compatible. The SN65HVD255 and SN65HVD257 devices have a 5-V ( $V_{CC}$ ) level RXD output. TXD is internally pulled up to  $V_{CC}$  and S is internally pulled down to GND.

---

#### NOTE

TXD is internally pulled up to  $V_{CC}$  and the S pin is internally pulled down to GND. However, the internal bias may only put the device into a known state if the pins float. The internal bias may be inadequate for system-level biasing. TXD pullup strength and CAN bit timing require special consideration when the SN65HVD25x devices are used with an open-drain TXD output on the CAN controller. An adequate external pullup resistor must be used to ensure that the CAN controller output of the  $\mu P$  maintains adequate bit timing input to the SN65HVD25x devices.

---

### 9.4.5.2 5-V $V_{CC}$ With $V_{RXD}$ RXD Output Supply Devices (SN65HVD256)

This device is a 5-V  $V_{CC}$  CAN transceiver with a separate supply for the RXD output,  $V_{RXD}$ . The digital inputs are 5-V and 3.3-V compatible. The SN65HVD256 device has a  $V_{RXD}$  level RXD output. TXD remains weakly pulled up to  $V_{CC}$ .

---

#### NOTE

On device versions with a  $V_{RXD}$  supply that shifts the RXD output level, the input pins of the device remain the same. TXD remains weakly pulled up to  $V_{CC}$  internally. Thus, a small  $I_{IH}$  current flows if the TXD input is used below  $V_{CC}$  levels.

---

### 9.4.5.3 5-V $V_{CC}$ with FAULT Open-Drain Output Device (SN65HVD257)

The SN65HVD257 device has a FAULT output pin (open-drain). FAULT must be pulled up to  $V_{CC}$  or I/O supply level through an external resistor.

---

#### NOTE

Because the FAULT output pin is open-drain, it actively pulls down when there is no fault and becomes high-impedance when a fault condition is detected. An external pullup resistor to the  $V_{CC}$  or I/O supply of the system must be used to pull the pin high to indicate a fault to the host microprocessor. The open-drain architecture makes the fault pin compatible with 3.3-V and 5-V I/O-level systems. The pullup current, selected by the pullup resistance value, must be as low as possible while achieving the desired voltage level output in the system with margin against noise.

---

## 10 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 10.1 Application Information

#### 10.1.1 Bus Loading, Length, and Number of Nodes

The ISO 11898 standard states that a CAN bus should have a maximum of 30 nodes, be less than 40 meters from end to end, and should have no stubs greater than 0.3 meters. However, with careful design, users can have longer cables, longer stub lengths, and many more nodes to a bus. A large number of nodes requires a transceiver with high input impedance, such as the SN65HVD25x family devices.

Many CAN organizations and standards have scaled the use of CAN for applications outside the original ISO11898 standard. They have made system level trade-offs for data rate, cable length, and parasitic loading of the bus. Examples of some of these specifications are: ARINC825, CANopen, DeviceNet, and NMEA200.

A CAN network design is a series of trade-offs, but these devices operate over wide common-mode range. In ISO11898-2, the driver differential output is specified with a 60- $\Omega$  load (the two 120- $\Omega$  termination resistors in parallel) and the differential output must be greater than 1.5 V. The SN65HVD25x devices are specified to meet the 1.5-V requirement with a 45- $\Omega$  load incorporating the worst case including parallel transceivers. The differential input resistance of the SN65HVD25x devices is a minimum of 30 K $\Omega$ . If 167 SN65HVD25x family transceivers are in parallel on a bus, this is equivalent to a 180- $\Omega$  differential load worst case. That transceiver load of 180  $\Omega$  in parallel with the 60  $\Omega$  gives a total 45  $\Omega$ . Therefore, the SN65HVD25x family theoretically supports over 167 transceivers on a single bus segment with margin to the 1.2-V minimum differential input at each node. However, CAN network design margin must be given for signal loss across the system and cabling, parasitic loadings, network imbalances, ground offsets, and signal integrity; thus a practical maximum number of nodes is typically much lower. Bus length may also be extended beyond the original ISO11898 standard of 40 m by careful system design and data-rate tradeoffs. For example, CAN open network design guidelines allow the network to be up to 1 km with changes in the termination resistance, cabling, less than 64 nodes, and a significantly lowered data rate.

This flexibility in CAN network design is one of the key strengths of the various extensions and additional standards that have been built on the original ISO11898 CAN standard. In using this flexibility comes the responsibility of good network design and balancing these tradeoffs.

## 10.2 Typical Applications

### 10.2.1 Typical 5-V Microcontroller Application

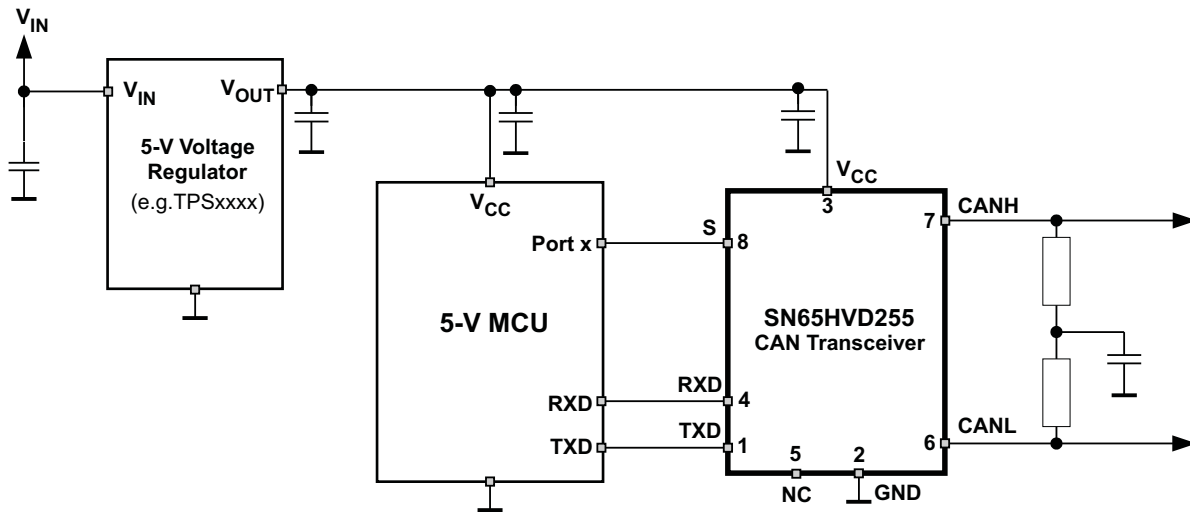


Figure 17. Typical 5-V Application

#### 10.2.1.1 Design Requirements

##### 10.2.1.1.1 CAN Termination

The ISO11898 standard specifies the interconnect to be a twisted-pair cable (shielded or unshielded) with 120-Ω characteristic impedance ( $Z_0$ ). Resistors equal to the characteristic impedance of the line must be used to terminate both ends of the cable to prevent signal reflections. Unterminated drop lines (stubs) connecting nodes to the bus must be kept as short as possible to minimize signal reflections. The termination may be on the cable or in a node, but if nodes may be removed from the bus, the termination must be carefully placed so that it is not removed from the bus.

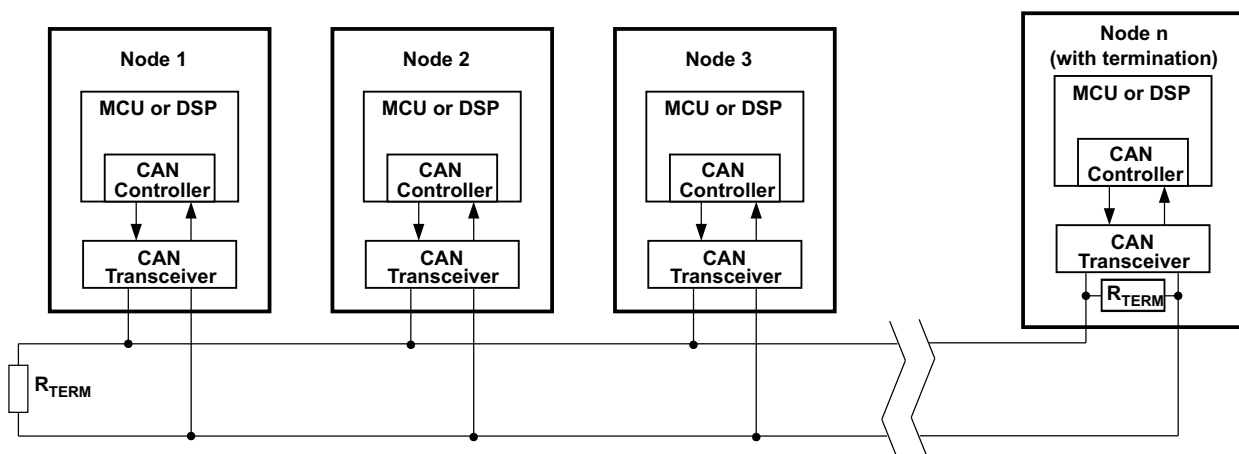
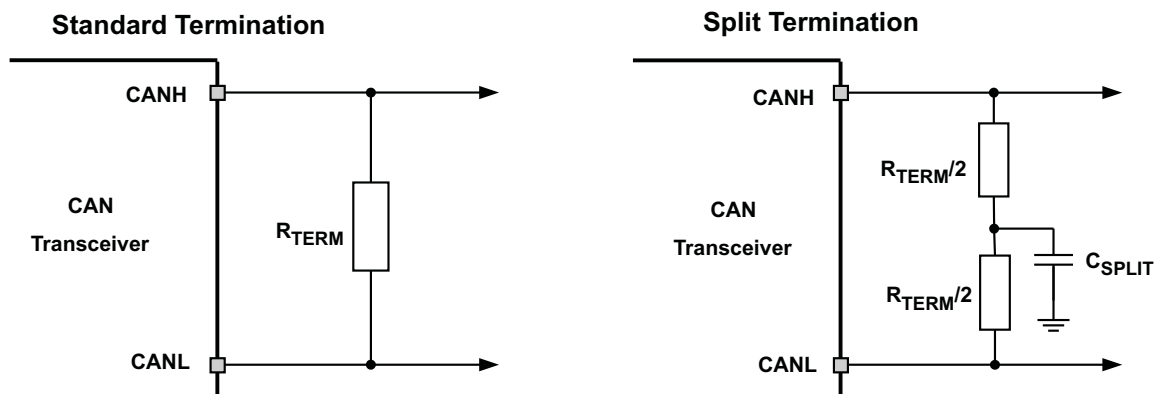


Figure 18. Typical CAN Bus

Termination may be a single 120-Ω resistor at the end of the bus either on the cable or in a terminating node. If filtering and stabilization of the common mode voltage of the bus is desired, then split termination may be used (see Figure 19). Split termination improves the electromagnetic emissions behavior of the network by eliminating fluctuations in the bus common-mode voltages at the start and end of message transmissions.

## Typical Applications (continued)



**Figure 19. CAN Bus Termination Concepts**

### 10.2.1.2 Detailed Design Procedure

#### 10.2.1.2.1 Example: Functional Safety Using the SN65HVD257 in a Redundant Physical Layer CAN Network Topology

CAN is a standard linear bus topology using 120-Ω twisted-pair cabling. The SN65HVD257 CAN device includes several features to use the CAN physical layer in nonstandard topologies with only one CAN link layer controller (μP) interface. This allows much greater flexibility in the physical topology of the bus while reducing the digital controller and software costs. The combination of RXD DTO and the FAULT output allows great flexibility, control, and monitoring of these applications.

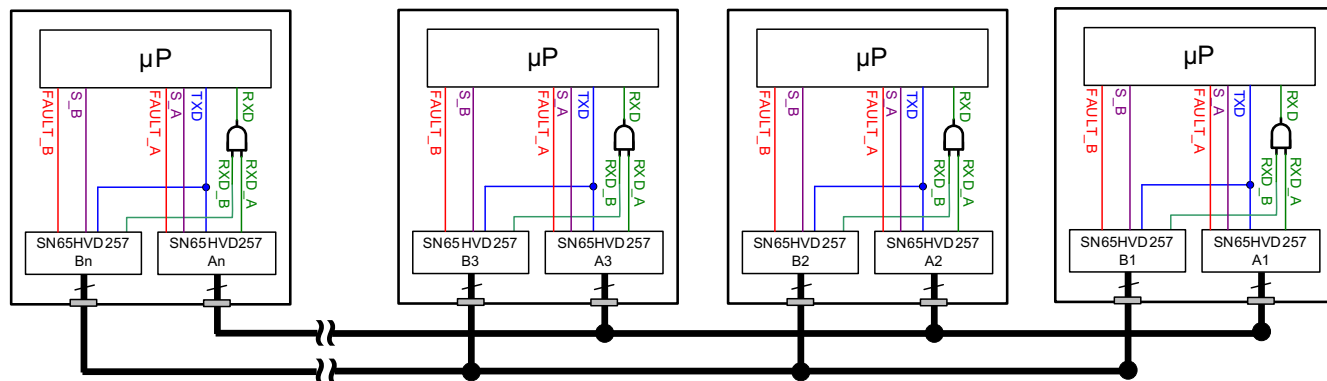
A simple example of this flexibility is to use two SN65HVD257 devices in parallel with an AND gate to achieve redundancy (parallel) of the physical layer (cabling and PHYs) in a CAN network.

For the CAN bit-wise arbitration to work, the RXD outputs of the transceivers must connect through AND gate logic so that a dominant bit (low) from any of the branches is received by the link layer logic (μP) and appears to the link layer and above as a single physical network. The RXD DTO feature prevents a bus stuck dominant fault in a single branch from taking down the entire network by forcing the RXD pin for the transceivers on the branch with the fault back to the recessive after the  $t_{RXD\_DTO}$  time. The remaining branch of the network continues to function. The FAULT pin of the transceivers on the branch with the fault indicates this through the FAULT output to their host processors, which diagnose the failure condition. The S pin (silent mode pin) may be used to put a branch in silent mode to check each branch for other faults. Therefore, it is possible to implement a robust and redundant CAN network topology in a very simple and low-cost manner.

These concepts can be expanded into more complicated and flexible CAN network topologies to solve various system-level challenges with a networked infrastructure.



## Typical Applications (continued)

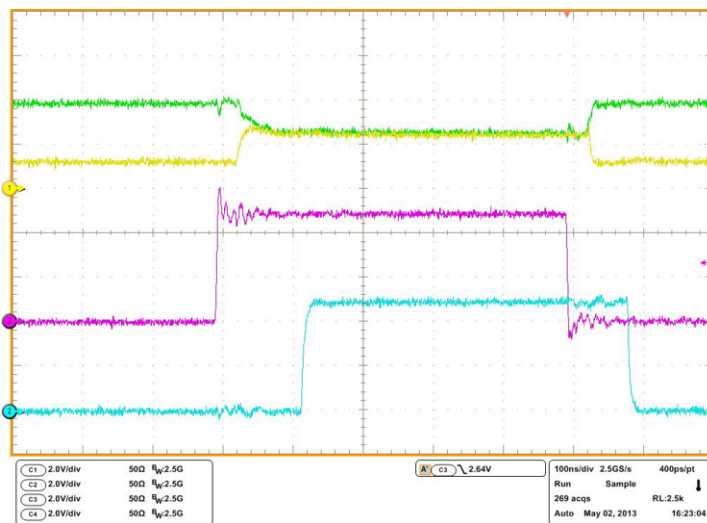


- CAN nodes with termination are PHY A, PHY B, PHY An and PHY Bn.
- RXD DTO prevents a single branch-stuck-dominant condition from blocking the redundant branch through the AND logic on RXD. The transceivers signal a received bus stuck dominant fault through the FAULT pin. The system detects which branch is stuck dominant and issues a system warning. Other network faults on a single branch that appear as recessive (not blocking the redundant network) may be detected through diagnostic routines and using the Silent Mode of the PHYs to use only one branch at a time for transmission during diagnostic mode. This combination allows robust fault detection and recovery within single branches so that they may be repaired and again provide redundancy of the physical layer.

**Figure 20. Typical Redundant Physical Layer Topology Using the SN65HVD257 Device**

### 10.2.1.3 Application Curves

Figure 21 shows the typical loop delay through the transceiver based on the differential resistive load between CANH and CANL.

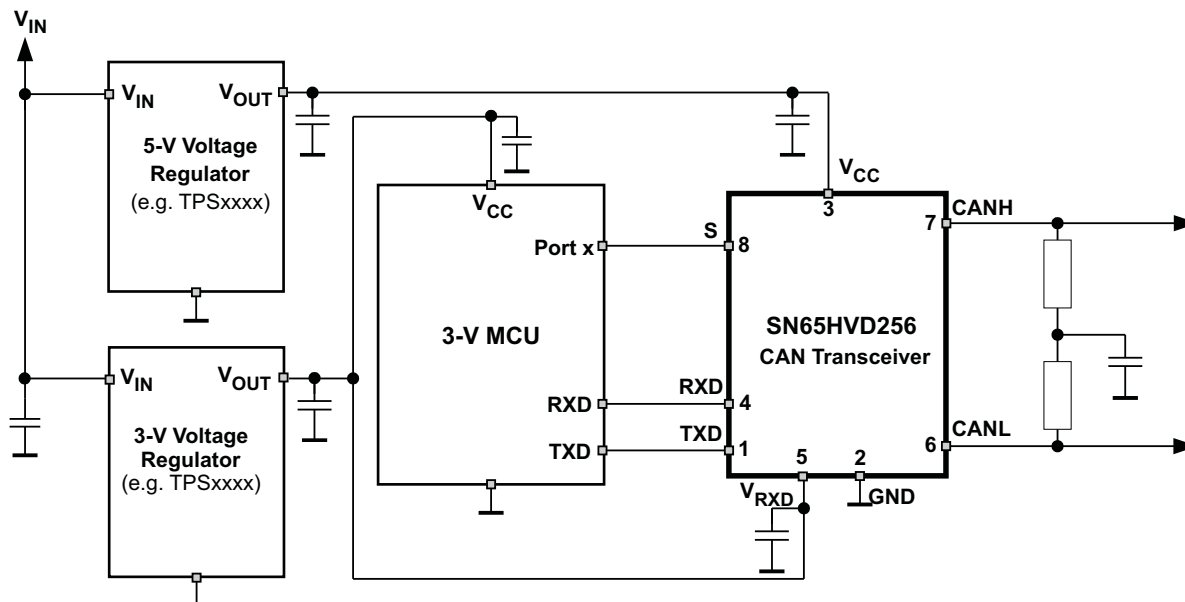


**Figure 21. Typical TXD to RXD Loop Delay**

## Typical Applications (continued)

### 10.2.2 Typical 3.3-V Microcontroller Application

The SN65HVD256 device has a second supply voltage pin used for level shifting the input and output pins. This can be used for applications where there is a 3.3-V microcontroller and a 5-V CAN transceiver.



**Figure 22. Typical 3.3-V Application**

## 11 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, each supply must be decoupled with a 100-nF ceramic capacitor located as close as possible to the supply pins. The TPS76350 device is a linear voltage regulator suitable for the 5-V supply rail.

## 12 Layout

### 12.1 Layout Guidelines

For the PCB design to be successful, start with the design of the protection and filtering circuitry because ESD and EFT transients have a wide frequency bandwidth from approximately 3-MHz to 3-GHz and high frequency layout techniques must be applied during PCB design. On chip IEC ESD protection is good for laboratory and portable equipment but is usually not sufficient for EFT and surge transients occurring in industrial environments. Therefore, robust and reliable bus node design requires the use of external transient protection devices at the bus connectors. Placement at the connector also prevents these harsh transient events from propagating further into the PCB and system.

Use  $V_{CC}$  and ground planes to provide low inductance.

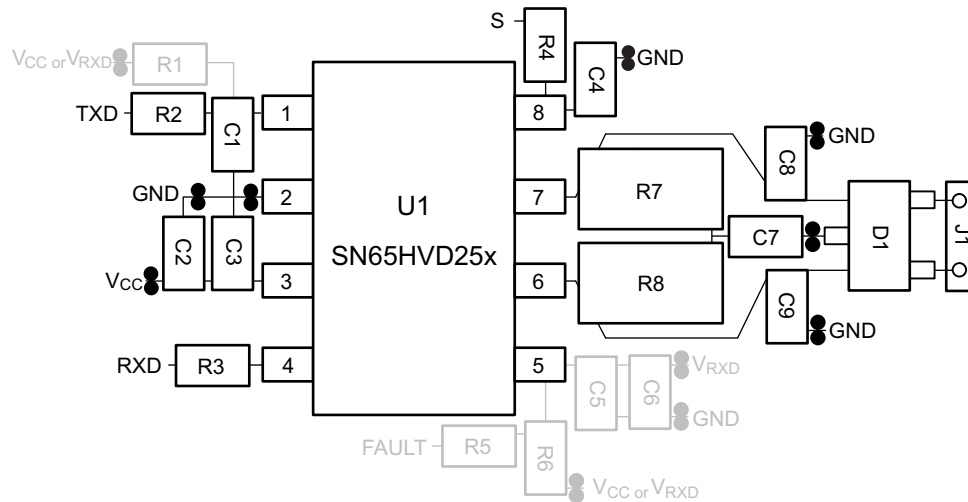
#### NOTE

High frequency current follows the path of least inductance and not the path of least resistance.

Design the bus protection components in the direction of the signal path. Do not force the transient current to divert from the signal path to reach the protection device. Below is a list of layout recommendations when designing a CAN transceiver into an application.

- **Transient Protection on CANH and CANL:** Transient Voltage Suppression (TVS) and capacitors (D1, C5 and C7 shown in [Figure 23](#)) can be used to protect the system level transients like EFT, IEC ESD, and Surge. These devices must be placed as close to the connector as possible. This prevents the transient energy and noise from penetrating into other nets on the board.
- **Bus Termination on CANH and CANL:** [Figure 23](#) shows split termination where the termination is split into two resistors, R5 and R6, with the center or split tap of the termination connected to ground through capacitor C6. Split termination provides common mode filtering for the bus. When termination is placed on the board instead of directly on the bus, care must be taken to ensure the terminating node is not removed from the bus, as this causes signal integrity issues if the bus is not properly terminated on both ends.
- **Decoupling Capacitors on  $V_{CC}$  and  $V_{RXD}$ :** Bypass and bulk capacitors must be placed as close as possible to the supply pins of transceiver (examples are C2, C3, C5, and C6).
- **Ground and power connections:** Use at least two vias for  $V_{CC}$ ,  $V_{IO}$ , and ground connections of bypass capacitors and protection devices to minimize trace and via inductance.
- **Digital inputs and outputs:** To limit current of digital lines, serial resistors may be used. Examples are R1, R2, R3, R4, and R5.
- **Filtering noise on digital inputs and outputs:** To filter noise on the digital I/O lines, a capacitor may be used close to the input side of the I/O as shown by C1 and C4.
- **External pull-up resistors on input and output pins:** Because the internal pullup and pulldown biasing of the device is weak for floating pins, an external 1-k $\Omega$  to 10-k $\Omega$  pullup or pulldown resistor must be used to bias the state of the pins during transient events.
- **Fault Output Pin (SN65HVD257 only):** Because the FAULT output pin is an open drain output, an external pullup resistor is required to pull the pin voltage high for normal operation (R5).
- **$V_{RXD}$  Supply (SN65HVD256 only):** The SN65HVD256 device will need additional bypass capacitors for the  $V_{RXD}$  supply shown with C5 and C6.
- **TXD input pin:** If an open-drain host processor is used to drive the TXD pin of the device, an external pullup resistor between 1 k $\Omega$  and 10 k $\Omega$  must be used to help drive the recessive input state of the device (weak internal pullup resistor).

## 12.2 Layout Example



**Figure 23. Layout Example**

## 13 Device and Documentation Support

### 13.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

**Table 7. Related Links**

| PARTS      | PRODUCT FOLDER             | SAMPLE & BUY               | TECHNICAL DOCUMENTS        | TOOLS & SOFTWARE           | SUPPORT & COMMUNITY        |
|------------|----------------------------|----------------------------|----------------------------|----------------------------|----------------------------|
| SN65HVD255 | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> |
| SN65HVD256 | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> |
| SN65HVD257 | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> | <a href="#">Click here</a> |

### 13.2 Trademarks

All trademarks are the property of their respective owners.

### 13.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 13.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

| Orderable part number        | Status<br>(1) | Material type<br>(2) | Package   Pins | Package qty   Carrier | RoHS<br>(3) | Lead finish/<br>Ball material<br>(4) | MSL rating/<br>Peak reflow<br>(5) | Op temp (°C) | Part marking<br>(6) |
|------------------------------|---------------|----------------------|----------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---------------------|
| <a href="#">SN65HVD255D</a>  | Active        | Production           | SOIC (D)   8   | 75   TUBE             | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD255              |
| SN65HVD255D.A                | Active        | Production           | SOIC (D)   8   | 75   TUBE             | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD255              |
| <a href="#">SN65HVD255DR</a> | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD255              |
| SN65HVD255DR.A               | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD255              |
| SN65HVD255DRG4               | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD255              |
| SN65HVD255DRG4.A             | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD255              |
| <a href="#">SN65HVD256D</a>  | Active        | Production           | SOIC (D)   8   | 75   TUBE             | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD256              |
| SN65HVD256D.A                | Active        | Production           | SOIC (D)   8   | 75   TUBE             | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD256              |
| <a href="#">SN65HVD256DR</a> | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD256              |
| SN65HVD256DR.A               | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD256              |
| SN65HVD256DRG4               | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD256              |
| SN65HVD256DRG4.A             | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD256              |
| <a href="#">SN65HVD257D</a>  | Active        | Production           | SOIC (D)   8   | 75   TUBE             | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD257              |
| SN65HVD257D.A                | Active        | Production           | SOIC (D)   8   | 75   TUBE             | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD257              |
| <a href="#">SN65HVD257DR</a> | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD257              |
| SN65HVD257DR.A               | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HVD257              |

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

**(6) Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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## TAPE AND REEL INFORMATION



\*All dimensions are nominal

| Device         | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|----------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| SN65HVD255DR   | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |
| SN65HVD255DRG4 | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |
| SN65HVD256DR   | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |
| SN65HVD256DRG4 | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |
| SN65HVD257DR   | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

| Device         | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| SN65HVD255DR   | SOIC         | D               | 8    | 2500 | 340.5       | 336.1      | 25.0        |
| SN65HVD255DRG4 | SOIC         | D               | 8    | 2500 | 340.5       | 336.1      | 25.0        |
| SN65HVD256DR   | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| SN65HVD256DRG4 | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| SN65HVD257DR   | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |



## TUBE



\*All dimensions are nominal

| Device        | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (μm) | B (mm) |
|---------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| SN65HVD255D   | D            | SOIC         | 8    | 75  | 507    | 8      | 3940   | 4.32   |
| SN65HVD255D.A | D            | SOIC         | 8    | 75  | 507    | 8      | 3940   | 4.32   |
| SN65HVD256D   | D            | SOIC         | 8    | 75  | 507    | 8      | 3940   | 4.32   |
| SN65HVD256D.A | D            | SOIC         | 8    | 75  | 507    | 8      | 3940   | 4.32   |
| SN65HVD257D   | D            | SOIC         | 8    | 75  | 507    | 8      | 3940   | 4.32   |
| SN65HVD257D.A | D            | SOIC         | 8    | 75  | 507    | 8      | 3940   | 4.32   |



**D0008A**

# PACKAGE OUTLINE

**SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

## NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

**D0008A**

### SOIC - 1.75 mm max height

## SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



## SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

## EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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